

AMENDMENTS TO THE SPECIFICATION

Paragraph beginning at page 5, line 17

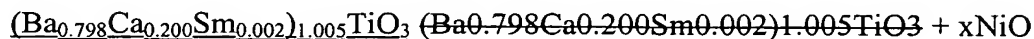
The element boron in the semiconductor ceramic is contained at about 0.2 to 20 mol% in the form of boron oxide. The content of the element boron here denotes the amount of the element boron with respect to the titanate site of the barium titanate in the semiconductor ceramic. In the case in which the element boron is contained in the semiconductor ceramic, it is necessary to produce a liquid phase with a composition ratio ~~AB₃O₅~~ AB₃O₅ (A: Ba site element, B: boron, O: oxygen), and to add the element at the Ba site additionally by 1/3 mol with respect to the element boron to improve sintering properties.

Paragraph beginning at page 6, line 15

The laminated product is baked in the reducing atmosphere to prevent oxidization of the internal electrode layers. Examples of the reducing atmosphere include an ~~H₂/N₂~~ H₂/N₂ atmosphere. The baking temperature and the baking time are not particularly limited, but are preferable 900 to 1,300°C for 0.5 to 5 hours.

Paragraph beginning at page 7, line 9

As starting materials, ~~BaCO₃, CaCO₃, TiO₂, Sm₂O₃~~ BaCO₃, CaCO₃, TiO₂, Sm₂O₃, and NiO were prepared, measured and mixed so as to have the following composition.

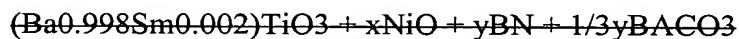


Paragraph beginning at page 7, line 18

By reduction baking of the obtained laminated product in an ~~H₂/N₂~~ H₂/N₂ atmosphere at 1,300°C for 2 hours, a laminated sintered compact was obtained. Ag was baked on the surface of the laminated sintered compact having exposed internal electrodes at 800°C as an external electrode, and the re-oxidization process was executed so as to obtain a laminated type semiconductor ceramic element 1 with an external electrode 9 formed on a laminated sintered compact 3 having semiconductor ceramic layers 5 and internal electrode layers 7 laminated alternately as shown in FIG. 1.

Paragraph beginning at page 9, line 4

As starting materials, ~~BaCO₃, TiO₂, Sm₂O₃~~ BaCO₃, TiO₂, Sm₂O₃, NiO and BN were prepared, measured and mixed so as to have the following composition.



Paragraph beginning at page 9, line 13

By reduction baking of the obtained laminated product in an ~~H₂/N₂~~ H₂/N₂ atmosphere at 1,000°C for 2 hours, a laminated sintered compact was obtained. Ag was baked on the surface of the laminated sintered compact with the exposed internal electrodes at 800°C as an external electrode, and a re-oxidization process was executed so as to obtain a laminated type semiconductor ceramic element 1 with an external electrode 9 formed on a laminated sintered compact 3 having semiconductor ceramic layers 5 and internal electrode layers 7 laminated alternately as shown in FIG. 1.